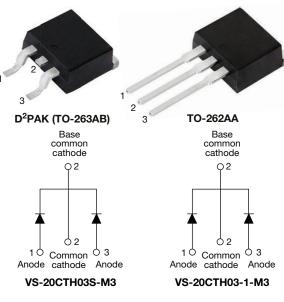
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# VS-20CTH03S-M3, VS-20CTH03-1-M3

# Vishay Semiconductors

Hyperfast Rectifier, 2 x 10 A FRED Pt®



## LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS				
I <sub>F(AV)</sub>	2 x 10 A			
V <sub>R</sub>	300 V			
V <sub>F</sub> at I <sub>F</sub>	0.85 V			
t <sub>rr</sub> max.	35 ns			
T <sub>J</sub> max.	175 °C			
Package	D <sup>2</sup> PAK (TO-263AB), TO-262AA			
Circuit configuration	Common cathode			

#### FEATURES

- Hyperfast recovery time
- Low forward voltage drop
- Low leakage current
- 175 °C operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Meets JESD 201, class 1A whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

## **DESCRIPTION / APPLICATIONS**

Vishay Semiconductors 300 V series are the state of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

## **MECHANICAL DATA**

**Case:** D<sup>2</sup>PAK (TO-263AB), TO-262AA

Molding compound meets UL 94 V-0 flammability rating **Terminal:** matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM R	ATINGS				
PARAMETER		SYMBOL	TEST CONDITIONS	MAX.	UNITS
Peak repetitive reverse voltage		V <sub>RRM</sub>		300	V
Average rectified forward current	per diode	I	T <sub>C</sub> = 160 °C	10	
Average rectilied forward current	per device	IF(AV)		20	А
Non-repetitive peak surge current		I <sub>FSM</sub>	T <sub>J</sub> = 25 °C	120	
Operating junction and storage tem	peratures	T <sub>J</sub> , T <sub>Stg</sub>		-65 to +175	°C

ELECTRICAL SPECIFICAT	IONS $(T_J$	= 25 °C unless otherwise specified)				
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	$V_{BR}, V_{R}$	I <sub>R</sub> = 100 μA	300	-	-	
Forward voltage	VF	I <sub>F</sub> = 10 A	-	1.05	1.25	V
Forward voltage	۷F	I <sub>F</sub> = 10 A, T <sub>J</sub> = 125 °C	-	0.85	0.95	
Deverse leekerse eurrent	1	$V_{R} = V_{R}$ rated	-	-	20	
Reverse leakage current	IR	$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	6	200	μΑ
Junction capacitance	CT	V <sub>R</sub> = 300 V	-	30	-	pF
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8	-	nH

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COMPLIANT

HALOGEN

FREE



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# **Vishay Semiconductors**

DYNAMIC RECOVERY CHARA	CTERIST	<b>ICS</b> (T <sub>C</sub> = 25 °C ι	unless otherwise s	specified	d)		
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t =$	50 A/µs, V <sub>R</sub> = 30 V	-	-	35	
Reverse recovery time	+	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t =$	100 A/ $\mu$ s, V <sub>R</sub> = 30 V	-	-	30	ns
	t <sub>rr</sub>	T <sub>J</sub> = 25 °C	$I_F = 10 \text{ A}$	-	31	-	A
		T <sub>J</sub> = 125 °C		-	42	-	
Peak recovery current	I	T <sub>J</sub> = 25 °C		-	2.4	-	
Feat recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C	dI <sub>F</sub> /dt = 200 A/µs V <sub>B</sub> = 200 V	-	5.6	-	~
Bowerse receivery charge	0	T <sub>J</sub> = 25 °C		-	36	-	nC
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	120	-	nC

THERMAL - MECHANICAL	SPECIFICAT	TIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65	-	175	°C
Thermal resistance, junction to case per diode	R <sub>thJC</sub>		-	-	1.5	°C/W
Thermal resistance, junction to ambient	R <sub>thJA</sub>		-	-	70	°C/W
Weight			-	2.0	-	g
Weight			-	0.07	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking daviag		Case style D <sup>2</sup> PAK (TO-263AB)		20CT	H03S	°C       °C/W       °C/W       g       oz.       kgf ⋅ cm
Marking device		Case style TO-262AA		20CT	H03-1	

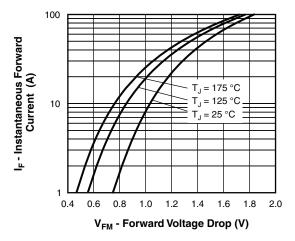


Fig. 1 - Maximum Forward Voltage Drop Characteristics

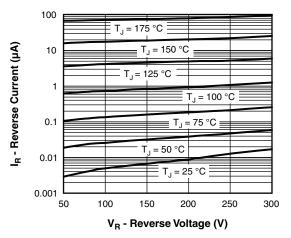


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



# VS-20CTH03S-M3, VS-20CTH03-1-M3

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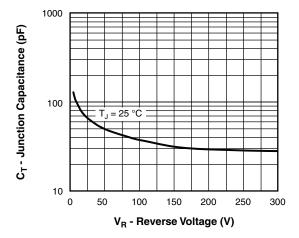


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

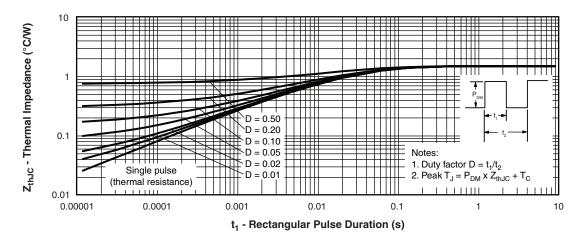
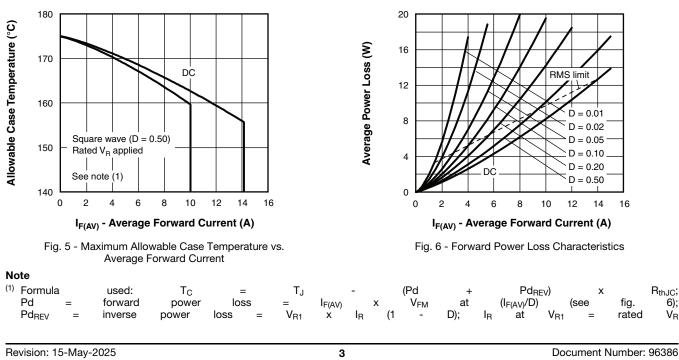


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics



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# VS-20CTH03S-M3, VS-20CTH03-1-M3

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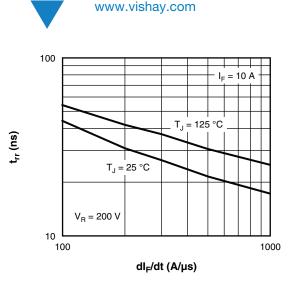


Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

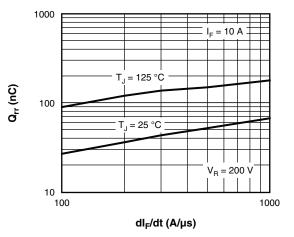


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt

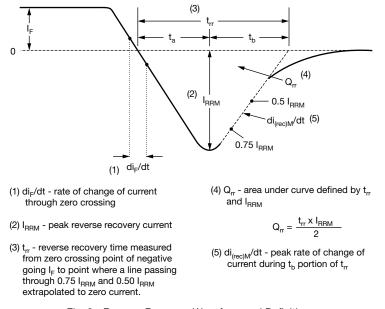
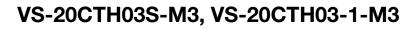


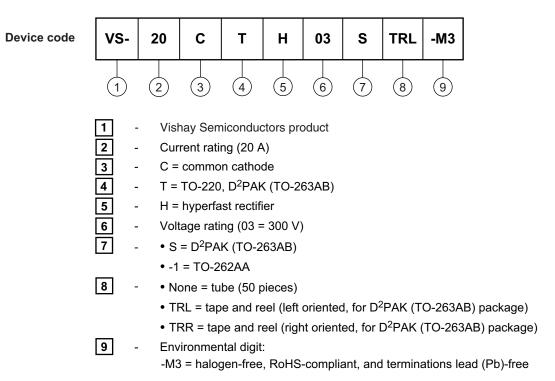
Fig. 9 - Reverse Recovery Waveform and Definitions



# **Vishay Semiconductors**

## **ORDERING INFORMATION TABLE**

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<b>ORDERING INFORMATION</b> (Exam	iple)	
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION
VS-20CTH03S-M3	50	Antistatic plastic tubes
VS-20CTH03STRL-M3	800	13" diameter plastic tape and reel
VS-20CTH03STRR-M3	800	13" diameter plastic tape and reel
VS-20CTH03-1-M3	50	Antistatic plastic tubes

	LINKS TO RELATE	D DOCUMENTS
Dimensions	D <sup>2</sup> PAK (TO-263AB)	www.vishay.com/doc?96164
Dimensions	TO-262AA	www.vishay.com/doc?96165
Part marking information	D <sup>2</sup> PAK (TO-263AB)	www.vishay.com/doc?95444
Part marking information	TO-262AA	www.vishay.com/doc?95443
Packaging information	D <sup>2</sup> PAK (TO-263AB)	www.vishay.com/doc?96424
SPICE model		www.vishay.com/doc?96583

**Vishay Semiconductors** 

D<sup>2</sup>PAK

## **DIMENSIONS** in millimeters and inches



ota	ted	90	°C
<u>S</u>	cale	<u>ə:</u> 8	:1

SYMBOL	MILLIM	ETERS	INC	HES	NOTES	
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
А	4.06	4.83	0.160	0.190		
A1	0.00	0.254	0.000	0.010		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
с	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	

SYMBOL	MILLIM	ETERS	INC	HES	NOTES
STNDUL	MIN.	MAX.	MIN.	MAX.	NOTES
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54	2.54 BSC		0.100 BSC	
Н	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	-	1.65	-	0.066	3
L2	1.27	1.78	0.050	0.070	
L3	0.25	BSC	0.010	BSC	
L4	4.78	5.28	0.188	0.208	

#### Notes

<sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

(3) Thermal pad contour optional within dimension E, L1, D1 and E1

<sup>(4)</sup> Dimension b1 and c1 apply to base metal only

(5) Datum A and B to be determined at datum plane H

(6) Controlling dimension: inches

<sup>(7)</sup> Outline conforms to JEDEC<sup>®</sup> outline TO-263AB

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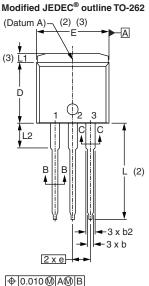
# **Outline Dimensions**

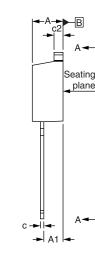


**Vishay Semiconductors** 

**TO-262AA** 

## **DIMENSIONS** in millimeters and inches





F D1 (3) (3) Section A - A Base (4) Plating b1. b3 metal ≰ c1 (4) -(b, b2)-Section B - B and C - C Scale: None





Diodes 1. - Anode (two die)/open (one die) 2., 4. - Cathode 3. - Anode

Lead assignments

SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190	
A1	2.03	3.02	0.080	0.119	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54	BSC	0.100	) BSC	
L	13.46	14.10	0.530	0.555	
L1	-	1.65	-	0.065	3
L2	3.56	3.71	0.140	0.146	

 <sup>(1)</sup> Dimensioning and tolerancing as per ASME Y14.5M-1994
<sup>(2)</sup> Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the second dimensioner of the second dimensis and the second dimensioner of the second dimensioner of the the outmost extremes of the plastic body (3)

Thermal pad contour optional within dimension E, L1, D1 and E1

<sup>(4)</sup> Dimension b1 and c1 apply to base metal only (5)

Controlling dimension: inches

(6) Outline conform to JEDEC® TO-262 except A1 (max.), b (min., max.), b1 (min.), b2 (max.), c (min.), c1(min.), c2 (max.), D (min.), E (max.), L1 (max.), L2 (min., max.)

Revision: 30-Nov-17

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